

Supplementary Materials

Fabrication of Gas-Sensor Chips Based on Silicon–Carbon Films Obtained by Electrochemical Deposition

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Table S1. Effect of air humidity on resistance drift at room temperature.

Humidity, %	Resistance, Ω			
	Type 1 (“pure” film)	Type 1 (film. doped with CuO)	Type 2 (“pure” film)	Type 2 (film doped with CuO)
25	45.248 ± 0.905	9.1965 ± 0.1839	29981 ± 600	159.09 ± 3.18
45	44.644 ± 0.893	9.0980 ± 0.1820	29431 ± 589	161.80 ± 3.24
65	44.355 ± 0.887	9.0576 ± 0.1812	29441 ± 589	157.82 ± 3.16
85	45.636 ± 0.913	9.3453 ± 0.1869	30310 ± 606	158.77 ± 3.18
95	46.007 ± 0.920	9.3655 ± 0.1873	30340 ± 607	161.64 ± 3.23